

Datasheet

E1.S 4TG2-P series

- PCIe Gen. 4x4, NVMe 1.4.
- iCell technology for power loss protection.
- Stable sustained performance.
- LDPC ECC engine supported.
- Dynamic thermal management.



Introduction

Innodisk E1.S 4TG2-P is an NVM Express SSD designed as the standard E1.S form factor with PCIe interface and 3D TLC NAND Flash. E1.S 4TG2-P supports PCIe Gen. 4x4, and it is compliant with NVMe 1.4 providing excellent performance. E1.S 4TG2-P with heatsink design dissipates heat generated from IC, making SSD performs more steadily. E1.S 4TG2-P has Die RAID protection to reduce bad blocks happening and optimize data integrity.

Innodisk E1.S 4TG2-P provides ultra-speed and high IOPS and offers maximum capacity up to 4TB, making the SSD optimal for server and heavy data workload applications.

E1.S

4TG2-P series

Contact us for more information
about the E1.S 4TG2-P.

Innodisk is a service-driven provider of industrial embedded flash and DRAM storage products and technologies, with a focus on the cloud computing, industrial/embedded, and aerospace and defense industries.

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Diagram PCBA

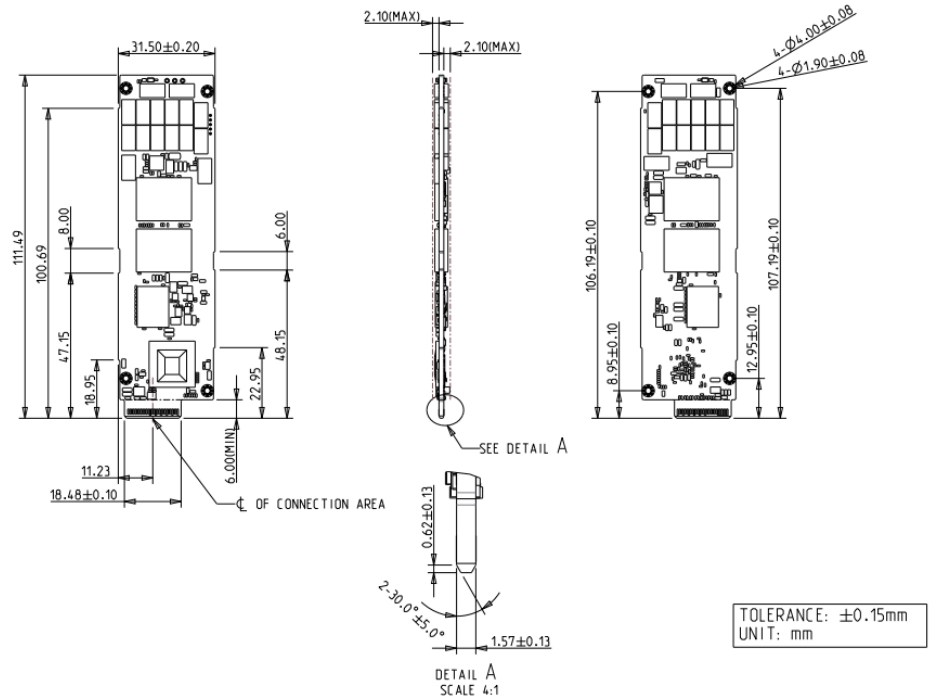
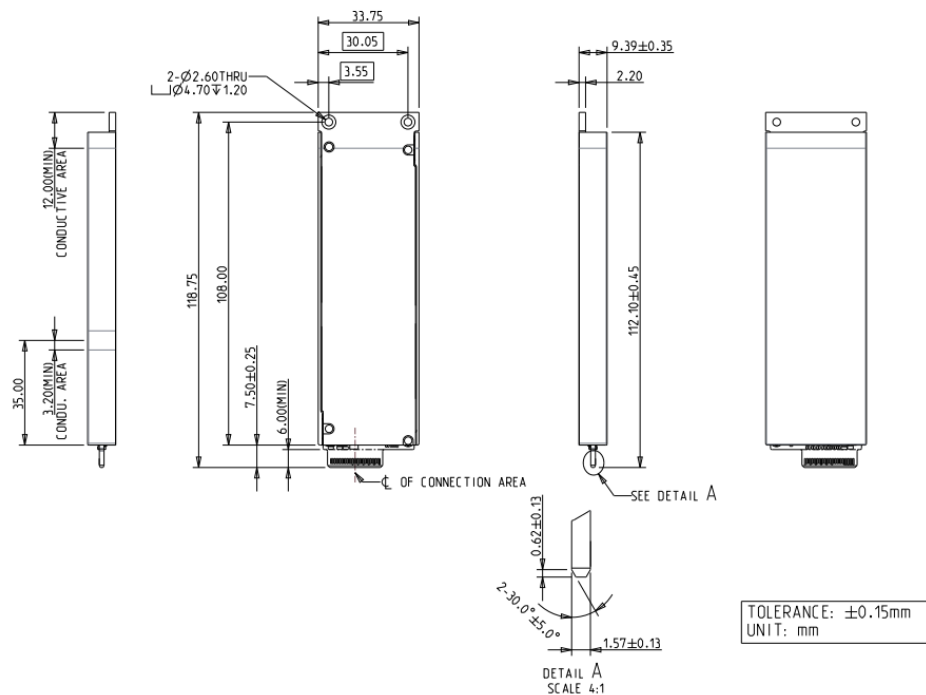


Diagram 9.5mm enclosure



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Specifications

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Interface	PCIe Gen. 4x4
Flash Type	3D TLC
P/E cycle	3,000
Capacity	512GB~8TB
Max. Channels	8
Sequential R/W (MB/sec, max.)	6,900/4,700
Max. Power Consumption	10.9W
Thermal Sensor	✓
External DRAM buffer	✓
H/W Write Protect	NA
Dimension (WxLxH)	9.5mm: 33.75 X 118.75 X 9.5 mm 15mm: 33.75 X 118.75 X 15 mm
Environment	Vibration: 20G @7~2000Hz Shock: 1500G @ 0.5ms Storage Temperature: -40°C ~ +85°C MTBF: 3 million hours

Ordering Information

Operation Temp.	512GB	1TB	2TB	4TB
Standard Grade (0°C ~ +70°C)	DGE1S-C12DP1KCAEFP%	DGE1S-01TDP2KCAEFP%	DGE1S-02TDP2KCAEFP%	DGE1S-04TDP2KCAEFP%
Industrial Grade (-40°C ~ +85°C)	DGE1S-C12DP1KWAEFP%	DGE1S-01TDP2KWAEFP%	DGE1S-02TDP2KWAEFP%	DGE1S-04TDP2KWAEFP%

Operation temperature based on temperature obtained from S.M.A.R.T.

%: H=9.5mm enclosure; H1=15mm enclosure

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